

PWS1065N65PR

Silicon Carbide MOSFET 650V, 65mΩ, 40A



重庆平伟半导体股份有限公司

Features

- Extremely low on-resistance $R_{DS(on)}$
- Robust body diode operation under hard commutation events
- Easy to Parallel and Simple to Drive
- Qualified according to JEDEC criteria



Applications

- SMPS
- Solar PV inverters
- EV charging infrastructure
- Energy storage and battery formation

100% DVDS Tested

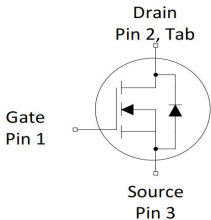
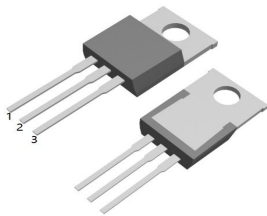
100%

Avalanche Tested

Product Summary

V_{DS}	650V
$R_{DS(on)}$ typ.	65mΩ
I_D	40A

TO-220AB-3L



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
PWS1065N65PR	S1065N65P	TO-220AB-3L	Tube	N/A	N/A	50

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Continuous drain current	I_D	40	A
$T_C = 25^\circ\text{C}$		28	
$T_C = 100^\circ\text{C}$			
Pulsed drain current ($T_C = 25^\circ\text{C}$)	$I_{D \text{ pulse}}$	119	A
Avalanche energy, single pulse ($L=5\text{mH}$)	E_{AS}	114	mJ
Gate-Source voltage,max.transient voltage	V_{GSmax}	-10/+22	V
Recommended operating values	V_{GSsop}	-5/+18	V
Power dissipation	P_{tot}	159	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	R_{thJC}	-	0.63	0.9	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	R_{thJA}	-	-	40	°C/W	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	650	-	-	V	$V_{GS}=0V, I_D=100\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.2	3.2	4.2	V	$V_{DS}=V_{GS}, I_D=5mA$
Zero gate voltage drain current	I_{DSS}	-	1	10	μA	$V_{DS}=650V, V_{GS}=0V$ $T_j=25^{\circ}C$
Gate-source leakage current	I_{GSS}	-	-	200	nA	$V_{GS}=22V, V_{DS}=0V$
		-	-	-200	nA	$V_{GS}=-10V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	65	75	mΩ	$V_{GS}=18V, I_D=20A$, $T_j=25^{\circ}C$
Transconductance	g_{fs}	-	13.0	-	S	$V_{DS}=20V, I_D=15A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	1144	-	pF	$V_{GS}=0V, V_{DS}=400V$, $f=1MHz$
Output Capacitance	C_{oss}	-	74	-		
Reverse Transfer Capacitance	C_{rss}	-	5	-		
Gate Total Charge	Q_G	-	40	-	nC	$V_{DS}=400V, I_D=20A$ $V_{GS}=-5V/18V$
Gate-Source charge	Q_{gs}	-	16	-		
Gate-Drain charge	Q_{gd}	-	12	-		
Turn-on delay time	$t_{d(on)}$	-	39	-	ns	$V_{GS}=-5/18V, V_{DD}=400V$, $R_G=10\Omega, I_D=20A$
Rise time	t_r	-	35	-		
Turn-off delay time	$t_{d(off)}$	-	26	-		
Fall time	t_f	-	12	-		
Turn-on energy	E_{on}	-	34	-	uJ	
Turn-off energy	E_{off}	-	44	-		
Gate resistance	R_G	-	3.6	-	Ω	$V_{GS}=0V, f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	3.42	-	V	$V_{GS} = -5V, I_{SD} = 10A$ $T_j = 25^{\circ}C$
		-	3.12	-		$T_j = 175^{\circ}C$
Body Diode Continuous Forward Current	I_S	-	40	-	A	$T_C = 25^{\circ}C$
		-	29	-	A	$T_C = 100^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	13	-	ns	$V_{GS} = -5V, I_{SD} = 20A,$ $V_R = 400V$ $di/dt = 1200A/us$
Body Diode Reverse Recovery Charge	Q_{rr}	-	39	-	nC	
Peak Reverse Recovery Current	I_{RRM}	-	5.0	-	A	

Typical Performance Characteristics

Fig 1: Output Characteristics $T_j=25^\circ\text{C}$

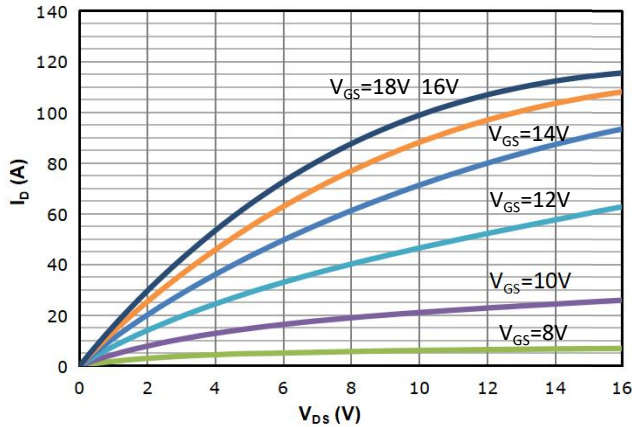


Fig 2: Output Characteristics $T_j=175^\circ\text{C}$

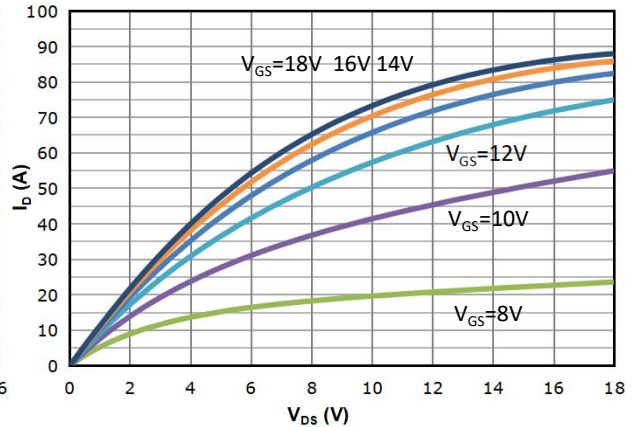


Fig 3: Transfer Characteristics

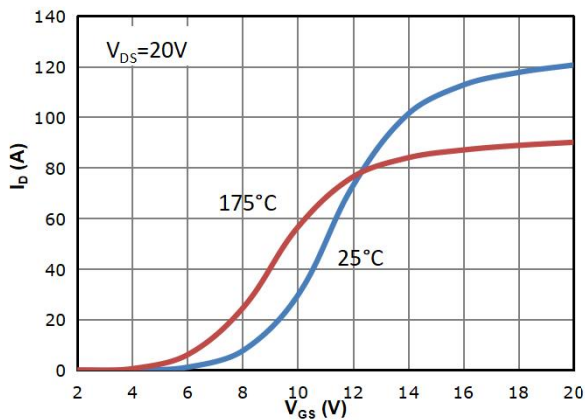


Fig 4: $R_{ds(on)}$ vs Drain Current and Gate Voltage

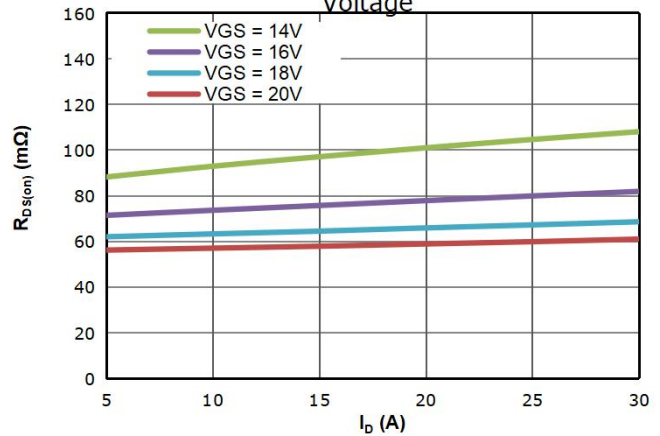


Fig 5: $R_{ds(on)}$ vs. Temperature

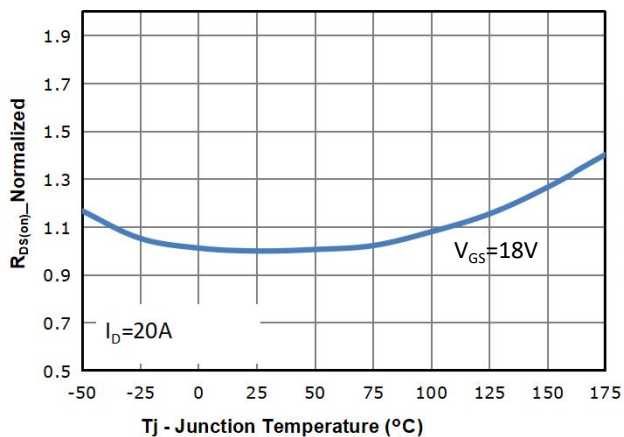


Fig 6: $V_{gs(th)}$ vs. Temperature

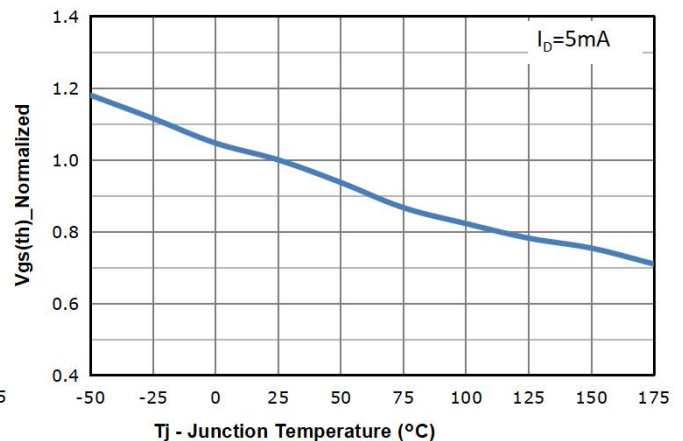


Fig 7: BVdss vs. Temperature

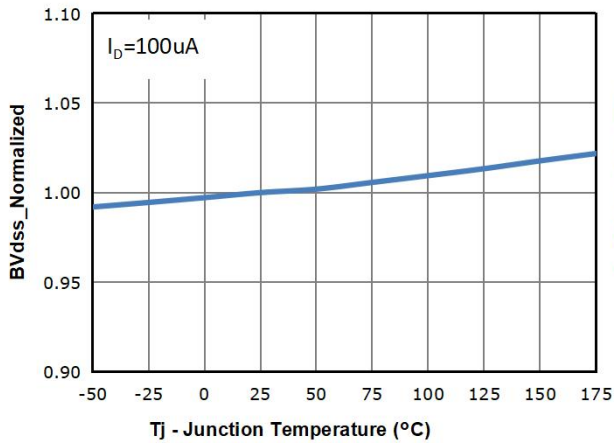


Fig 8: Capacitance Characteristics

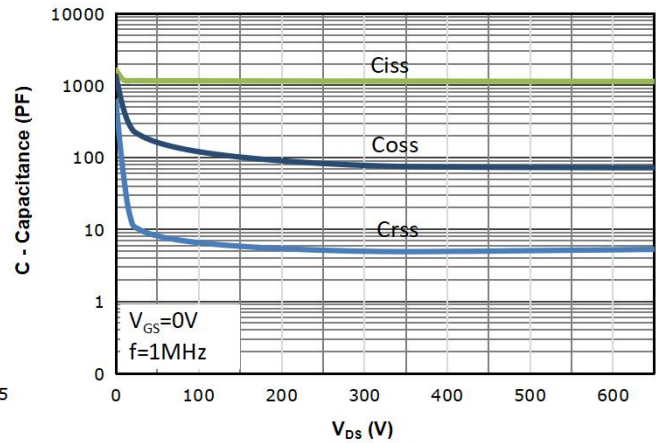


Fig 9: Gate Charge Characteristics

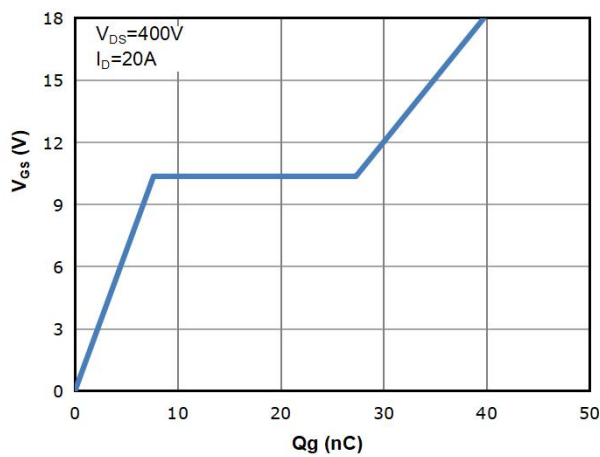


Fig 10: Body-diode Forward Characteristics

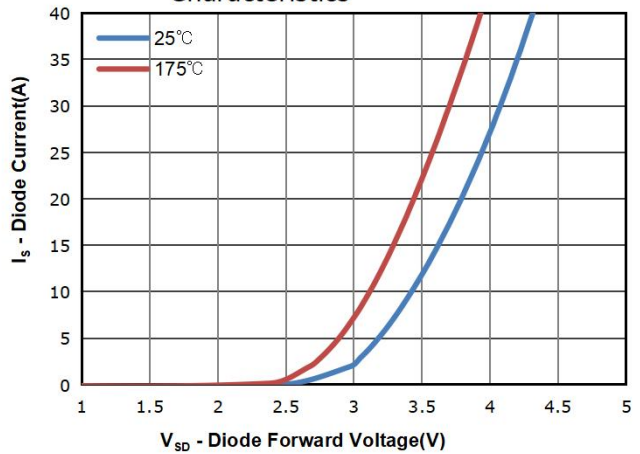


Fig 11: Power Dissipation

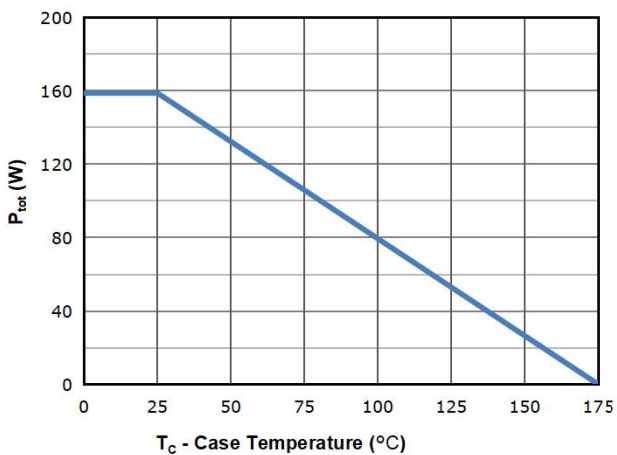


Fig 12: Drain Current Derating

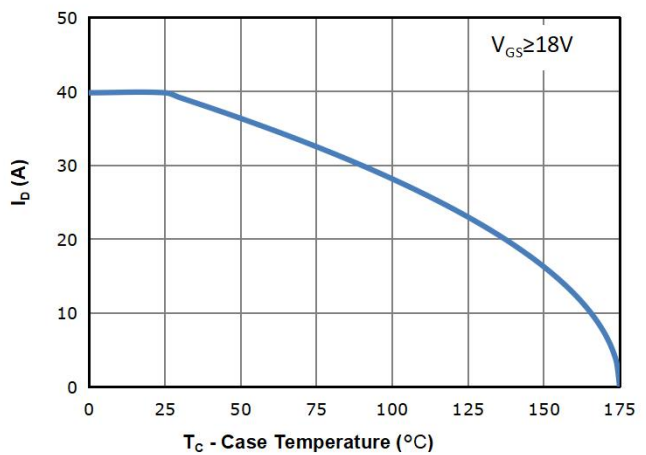




Fig 13: Safe Operating Area

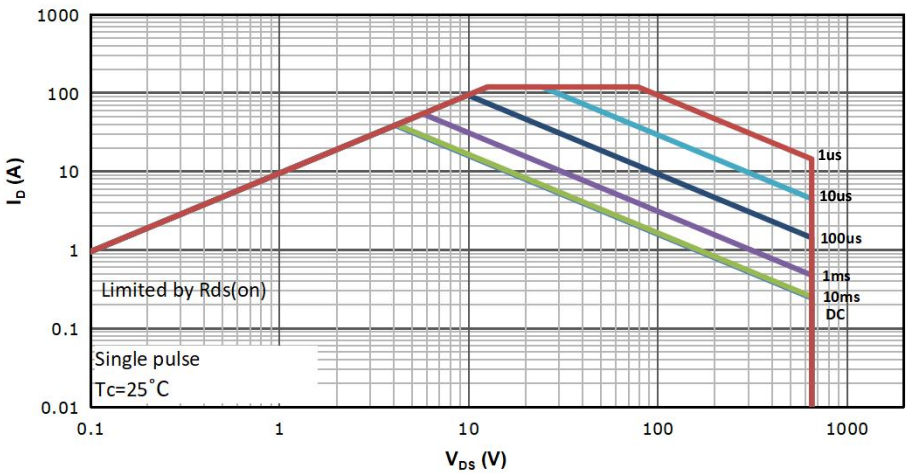
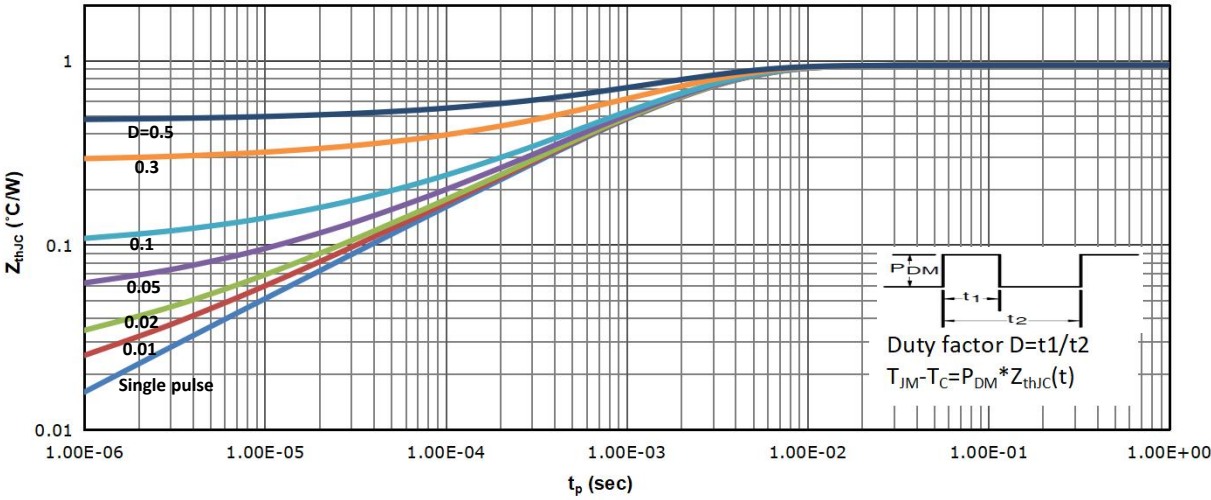
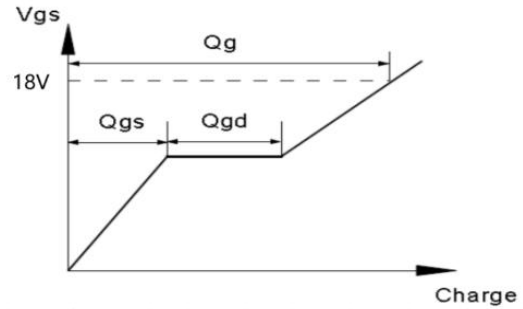
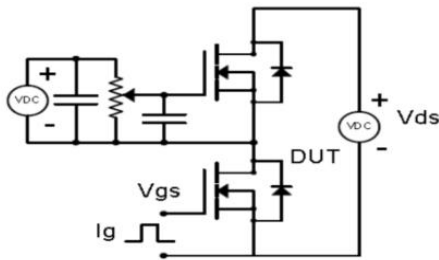


Fig 14: Max. Transient Thermal Impedance

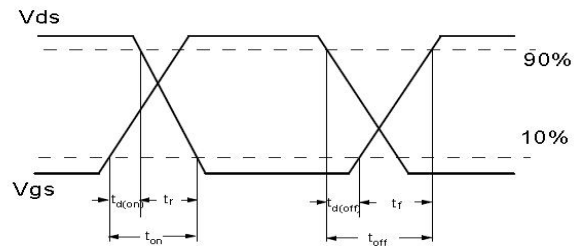
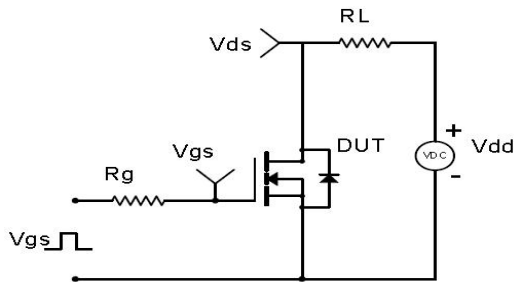


Test Circuit & Waveform

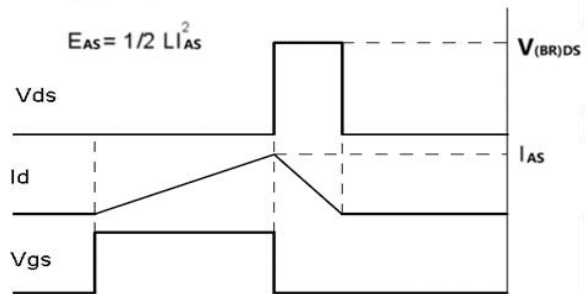
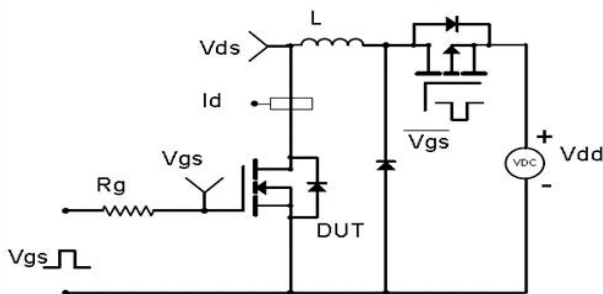
Gate Charge Test Circuit & Waveform



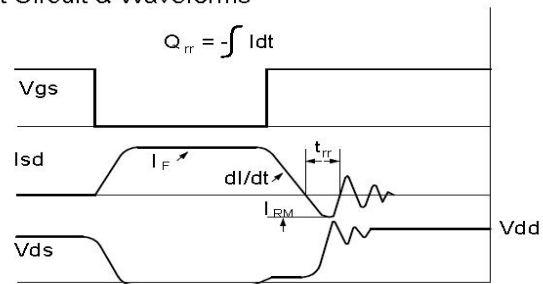
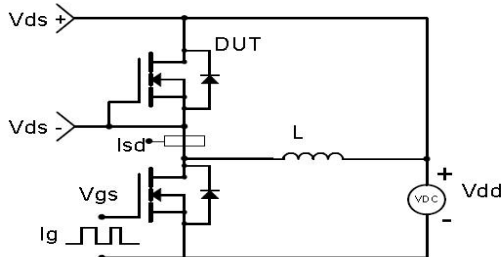
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



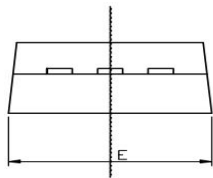
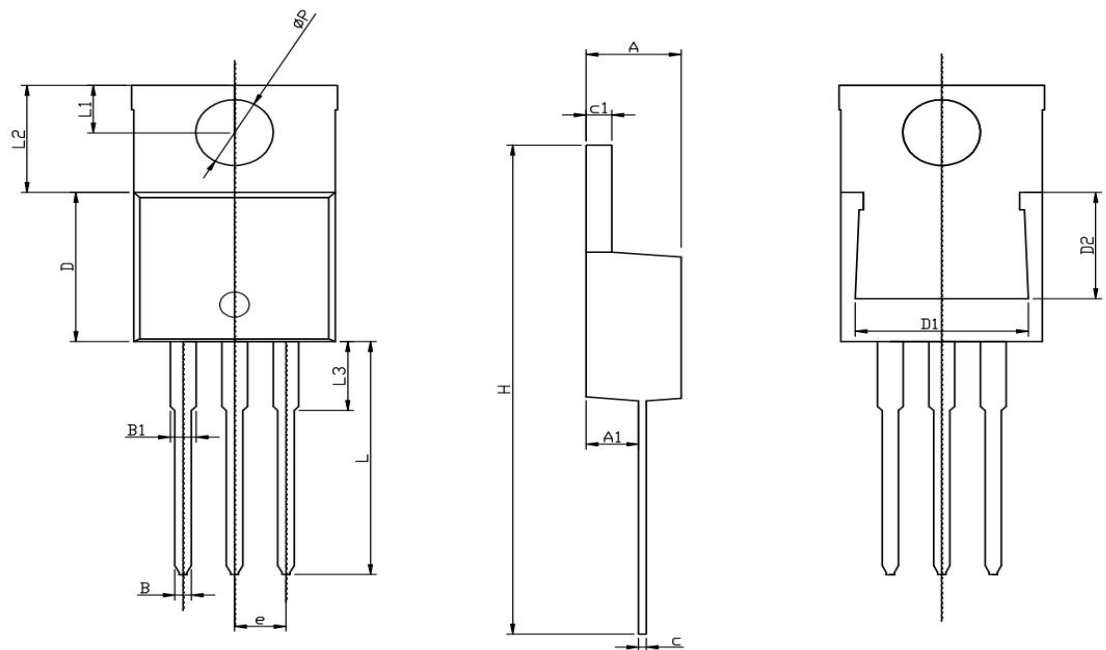
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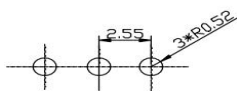


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Package Outline: TO-220AB-3L



RECOMMENDED LAND PATTERN



UNIT: mm

	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.45	2.60	2.70
B	0.72	0.82	0.92
B1	1.12	1.27	1.42
c	0.28	0.38	0.48
c1	1.17	1.27	1.37
D	8.46	8.66	8.86
D1	7.90	8.10	8.40
D2	5.50	5.70	5.90
e	2.45	2.55	2.65
E	9.85	10.15	10.45
H	28.00	28.50	29.00
ϕP		3.84	
L	13.1	13.6	14.1
L1	2.54	2.74	2.94
L2	6.04	6.24	6.44
L3	3.85	4.05	4.35

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

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